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| INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449) | | | ATTY. DOCKET NO. 57810-033 | | SERIAL NO. | |
| | | | APPLICANT Nobuhiko HAYASHI | | | |
| | | | FILING DATE February 28, 2002 | | GROUP | |

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| U.S. PATENT DOCUMENTS | | | | | | |
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| EXAMINER'S INITIALS | PATENT NO. | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
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| EXAMINER'S INITIALS | PATENT NO. | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
| | | | | | | Yes | No |
| <i>De</i> | 2000-164989 | 6/16/2000 | Japan (w/ English Abstract) | | | | |
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| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) | |
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| <i>De</i> | S. Nakamura et al., "Long lifetime violet InGa _N /Ga _N /AlGa _N -based semiconductor lasers", Journal of Oyo Denshi Bussei Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215. |
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| EXAMINER <i>Donna Hsu</i> | DATE CONSIDERED <i>Mar/03</i> |
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.